

STURCTURE OF THIN FILM TRANSISTOR AND MANUFACTURING METHOD THEREOF

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a thin film transistor for solving the drawbacks of the prior art is disclosed. The method includes steps of providing an insulating substrate, sequentially forming a source/drain layer, a primary gate insulating layer, and a first conducting layer on the insulating substrate, etching the first conducting layer to form a primary gate; sequentially forming a secondary gate insulating layer and a second conducting layer on the primary gate; and etching the second conducting layer to form a first secondary gate and a second secondary gate.